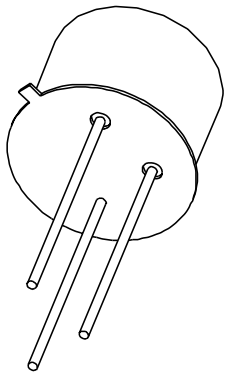


DATA SHEET



2N3019

NPN medium power transistor

Product specification
Supersedes data of September 1994
File under Discrete Semiconductors, SC04

1997 Jun 19

NPN medium power transistor

2N3019

FEATURES

- High current (max. 1 A)
- Low voltage (max. 80 V).

APPLICATIONS

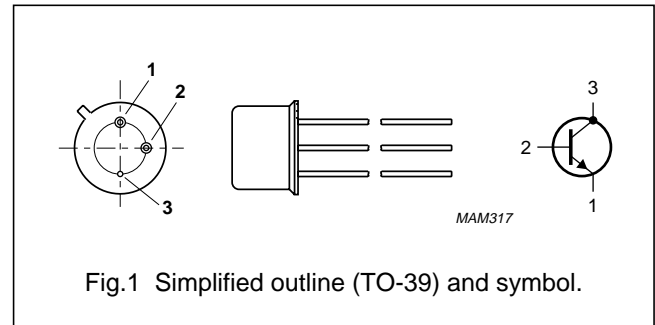
- Amplifier and switching circuits.

DESCRIPTION

NPN medium power transistor in a TO-39 metal package.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector, connected to case



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	140	V
V_{CEO}	collector-emitter voltage	open base	–	80	V
I_C	collector current (DC)		–	1	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	800	mW
		$T_{case} \leq 25\text{ }^\circ\text{C}$	–	5	W
h_{FE}	DC current gain	$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	100	300	
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 100\text{ MHz}$	100	–	MHz

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	140	V
V _{CEO}	collector-emitter voltage	open base	–	80	V
V _{EBO}	emitter-base voltage	open collector	–	7	V
I _C	collector current (DC)		–	1	A
I _{CM}	peak collector current		–	1	A
I _{BM}	peak base current		–	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	–	800	mW
		T _{case} ≤ 25 °C	–	5	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	200	°C
T _{amb}	operating ambient temperature		–65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	in free air	218	K/W
R _{th j-c}	thermal resistance from junction to case		35	K/W

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CHARACTERISTICS $T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 90\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 90\text{ V}; T_{amb} = 150\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$V_{CE} = 10\text{ V}$; note 1			
		$I_C = 0.1\text{ mA}$	50	–	
		$I_C = 10\text{ mA}$	90	–	
		$I_C = 150\text{ mA}$	100	300	
		$I_C = 150\text{ mA}; T_{case} = -55\text{ °C}$	40	–	
		$I_C = 500\text{ mA}$	50	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$	–	200	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$; note 1	–	500	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 150\text{ mA}; I_B = 15\text{ mA}$; note 1	–	1.1	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	12	pF
C_e	emitter capacitance	$I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$	–	60	pF
f_T	transition frequency	$I_C = 50\text{ mA}; V_{CE} = 10\text{ V}; f = 20\text{ MHz}$	100	–	MHz
F	noise figure	$I_C = 0.1\text{ mA}; V_{CE} = 5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$	–	4	dB

Note1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.01$.

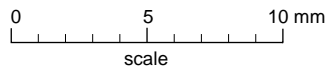
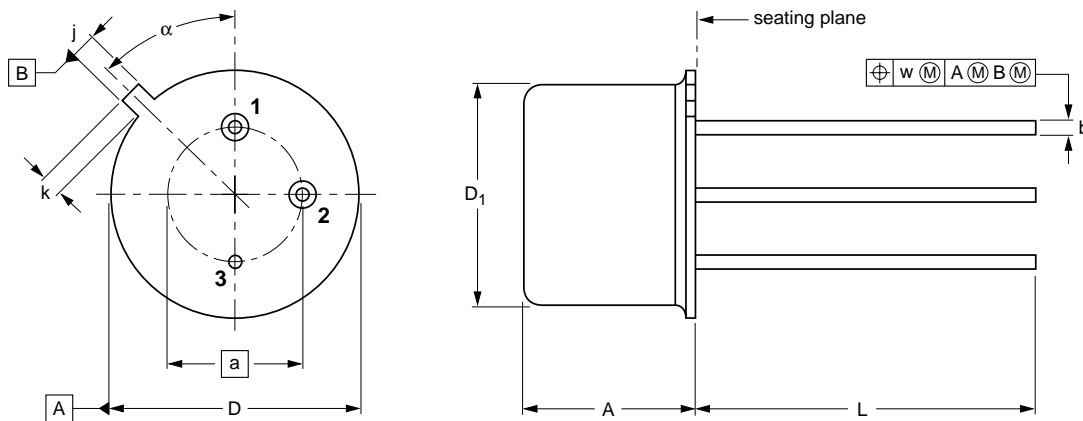
NPN medium power transistor

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PACKAGE OUTLINE

Metal-can cylindrical single-ended package; 3 leads

SOT5/11



DIMENSIONS (mm are the original dimensions)

UNIT	A	a	b	D	D ₁	j	k	L	w	α
mm	6.60 6.35	5.08	0.48 0.41	9.39 9.08	8.33 8.18	0.85 0.75	0.95 0.75	14.2 12.7	0.2	45°

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT5/11		TO-39				97-04-11

NPN medium power transistor

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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NPN medium power transistor

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